



SamHop Microelectronics Corp.

STU/D1855PL

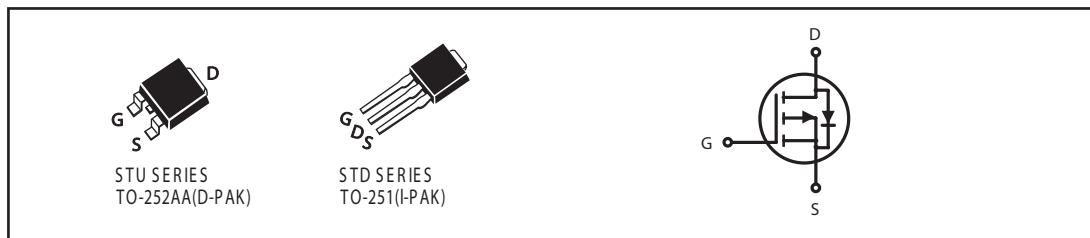
Apr,20 2005 ver1.1

P-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V _{DSS}	I _D	R _{DSON} (mΩ) Max
-55V	-15A	68 @ V _{GS} = -10V
		85 @ V _{GS} = -4.5V

FEATURES

- Super high dense cell design for low R_{DSON}.
- Rugged and reliable.
- TO-252 and TO-251 Package.



ABSOLUTE MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage Rating	V _{spike} ^d	60	V
Drain-Source Voltage	V _{DS}	-55	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous ^a @ T _a	25°C	-15	A
	70°C	-12	A
-Pulsed ^b	I _{DM}	-30	A
Drain-Source Diode Forward Current ^a	I _S	-10	A
Maximum Power Dissipation ^a	T _a =25°C	42	W
	T _a =70°C	28	
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Case	R _{θJC}	3	°C/W
Thermal Resistance, Junction-to-Ambient	R _{θJA}	50	°C/W

STU/D1855PL

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ C$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	V_{DSS}	$V_{GS} = 0V, I_D = -250\mu A$	-55			V
Zero Gate Voltage Drain Current	$I_{DS(on)}$	$V_{DS} = -44V, V_{GS} = 0V$		-1		μA
Gate-Body Leakage	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$		± 100		nA
ON CHARACTERISTICS^b						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.3	-1.8	-2.5	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = -10V, I_D = -10A$		50	68	m-ohm
		$V_{GS} = -4.5V, I_D = -6A$		65	85	m-ohm
On-State Drain Current	$I_{DS(on)}$	$V_{DS} = -5V, V_{GS} = -10V$	20			A
Forward Transconductance	g_{FS}	$V_{DS} = -15V, I_D = -10A$		12		S
DYNAMIC CHARACTERISTICS^c						
Input Capacitance	C_{ISS}	$V_{DS} = -30V, V_{GS} = 0V$ $f = 1.0MHz$		830	985	pF
Output Capacitance	C_{OSS}			110	125	pF
Reverse Transfer Capacitance	C_{RSS}			65	75	pF
SWITCHING CHARACTERISTICS^c						
Turn-On Delay Time	$t_{D(on)}$	$V_D = -30V,$ $I_D = -1A,$ $V_{GEN} = -10V,$ $R_{GEN} = 6 \text{ ohm}$		7.1	8	ns
Rise Time	t_r			22.7	26	ns
Turn-Off Delay Time	$t_{D(off)}$			59.3	68	ns
Fall Time	t_f			24.9	28	ns
Total Gate Charge	Q_g	$V_{DS} = -30V, I_D = -5A, V_{GS} = 10V$		16.7	19	nC
		$V_{DS} = -30V, I_D = -5A, V_{GS} = -4.5V$		8.1	9.5	nC
Gate-Source Charge	Q_{gs}	$V_{DS} = -30V, I_D = -5A,$ $V_{GS} = -10V$		1.9	2.6	nC
Gate-Drain Charge	Q_{gd}			4.1	4.7	nC

STU/D1855PL

ELECTRICAL CHARACTERISTICS ($T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ ^c	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS ^b						
Diode Forward Voltage	V_{SD}	$V_{GS} = 0V, I_S = -10A$		-0.9	-1.3	V

Notes

- a. Surface Mounted on FR4 Board, $t \leq 10\text{sec}$.
- b. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2\%$.
- c. Guaranteed by design, not subject to production testing.
- d. Guaranteed when external $R_g=6\text{ ohm}$ and $t_f < t_{f\max}$

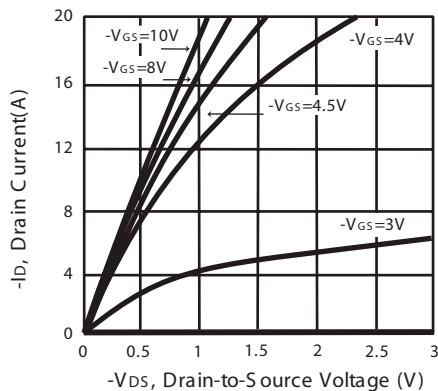


Figure 1. Output Characteristics

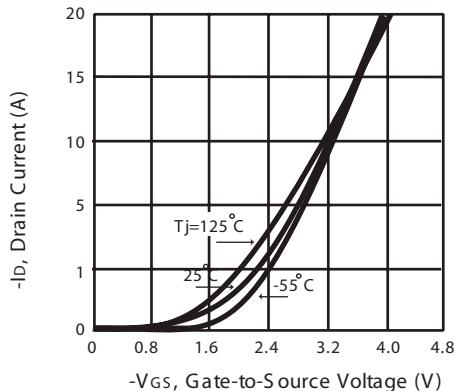


Figure 2. Transfer Characteristics

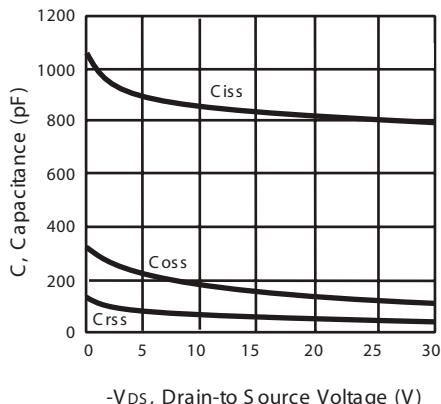


Figure 3. Capacitance

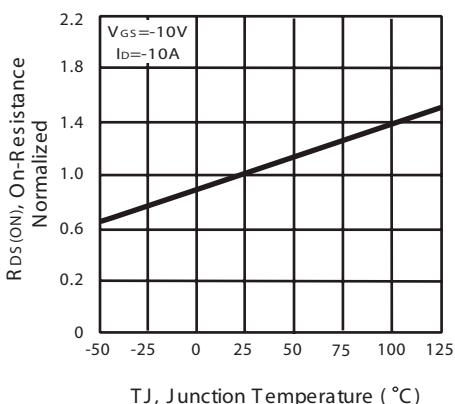
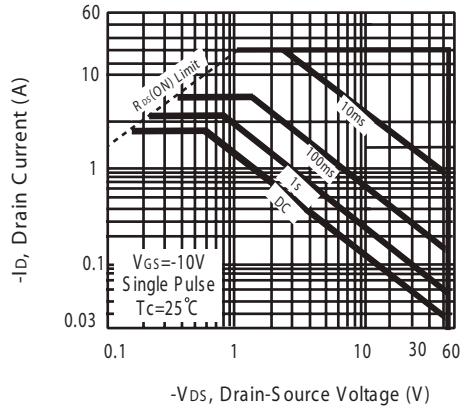
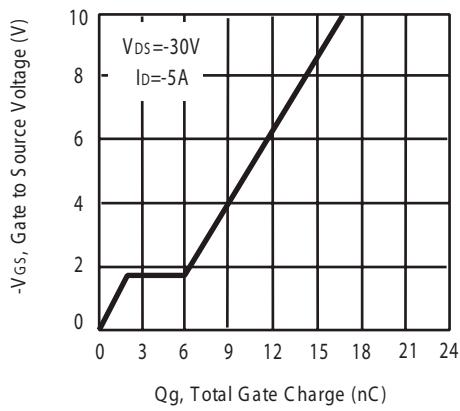
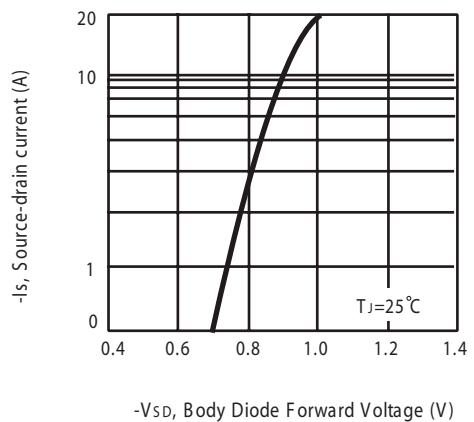
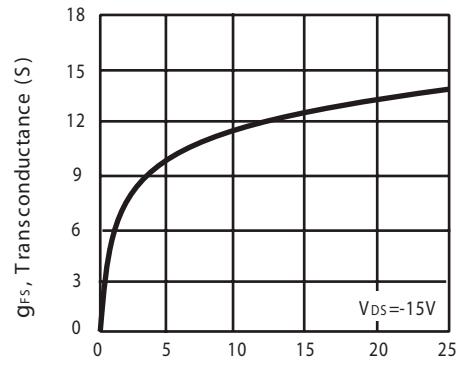
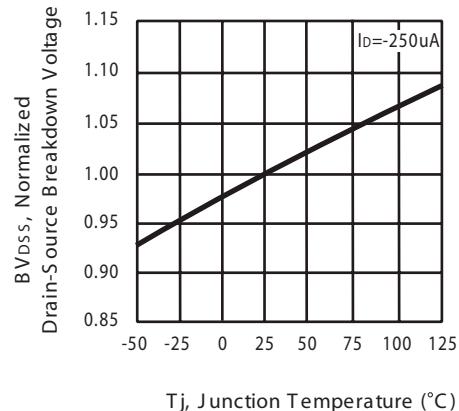
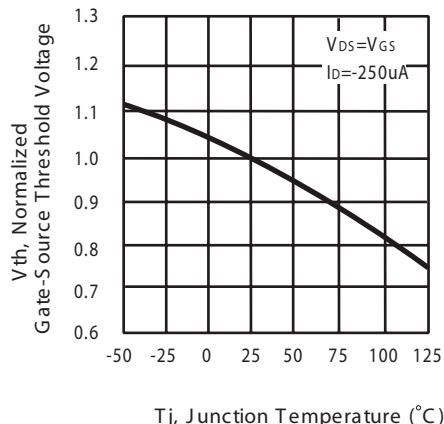


Figure 4. On-Resistance Variation with Temperature

STU/D1855PL



STU/D1855PL

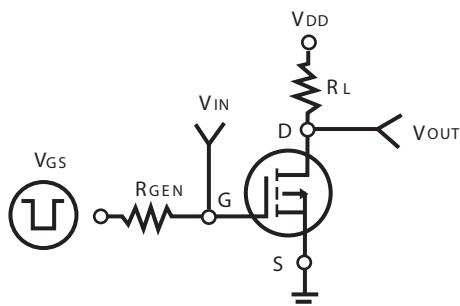


Figure 11. S switching Test Circuit

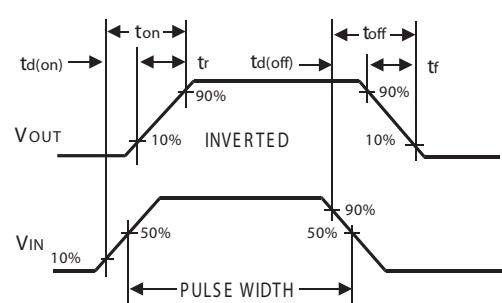
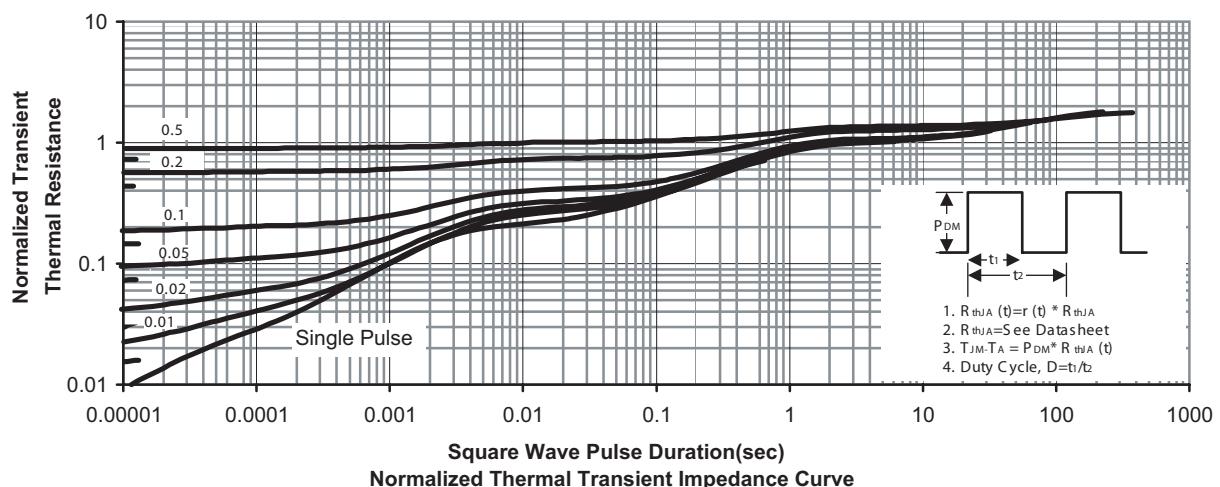


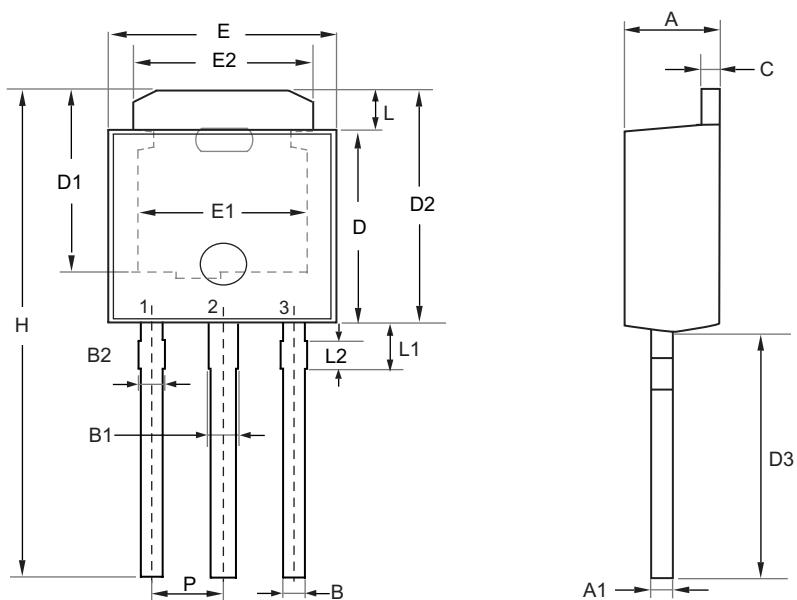
Figure 12. S switching Waveforms



STU/D1855PL

PACKAGE OUTLINE DIMENSIONS

TO-251

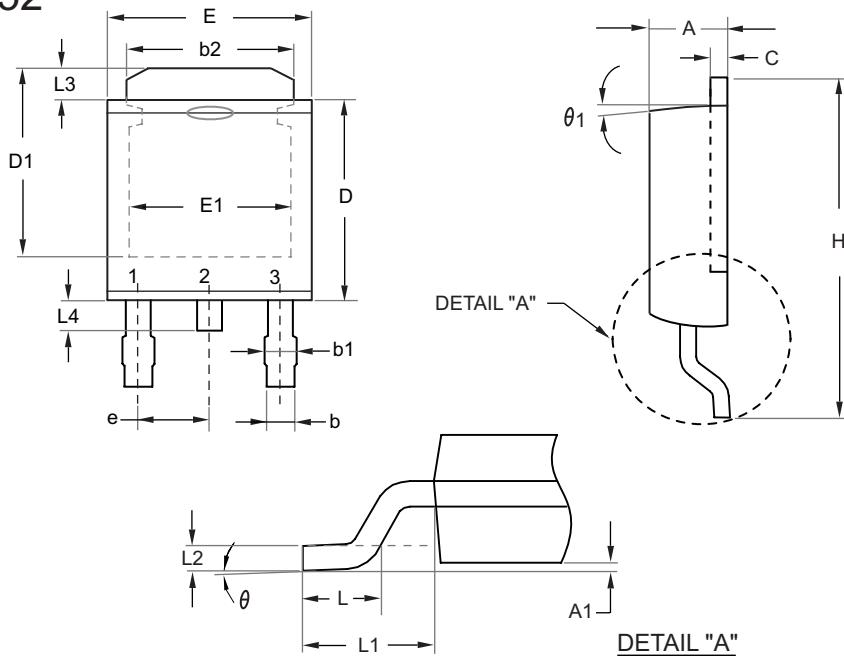


SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.350	0.650	0.014	0.026
B	0.400	0.800	0.016	0.031
B1	0.650	1.050	0.026	0.041
B2	0.500	0.900	0.020	0.035
C	0.400	0.600	0.016	0.024
D	5.300	5.700	0.209	0.224
D1	4.900	5.300	0.193	0.209
D2	6.700	7.300	0.264	0.287
D3	7.000	8.000	0.276	0.315
H	13.700	15.300	0.539	0.602
E	6.300	6.700	0.248	0.264
E1	4.600	4.900	0.181	0.193
E2	4.800	5.200	0.189	0.205
L	1.300	1.700	0.051	0.067
L1	1.400	1.800	0.055	0.071
L2	0.500	0.900	0.020	0.035
P	2.300 BSC		0.091 BSC	

STU/D1855PL

PACKAGE OUTLINE DIMENSIONS

TO-252

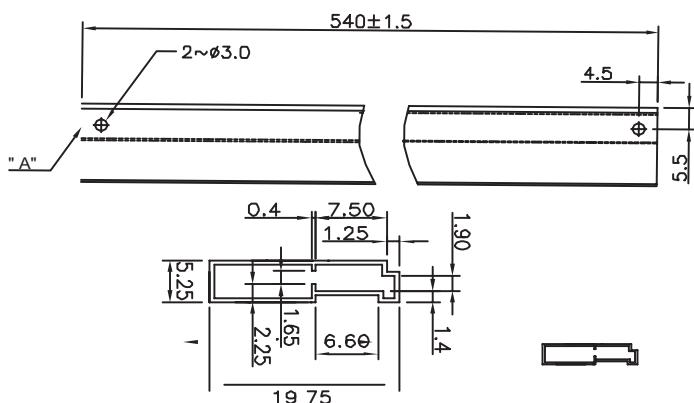


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.100	2.500	0.083	0.098
A1	0.000	0.200	0.000	0.008
b	0.400	0.889	0.016	0.035
b1	0.770	1.140	0.030	0.045
b2	4.800	5.460	0.189	0.215
C	0.400	0.600	0.016	0.024
D	5.300	6.223	0.209	0.245
D1	4.900	5.515	0.193	0.217
E	6.300	6.731	0.248	0.265
E1	4.400	5.004	0.173	0.197
e	2.290	REF	0.090	BSC
H	8.900	10.400	0.350	0.409
L	1.397	1.770	0.055	0.070
L1	2.743	REF.	0.108	REF.
L2	0.508	REF.	0.020	REF.
L3	0.890	1.700	0.035	0.067
L4	0.500	1.100	0.020	0.043
θ	0°	10°	0°	10°
θ1	7°	REF.	7°	REF.

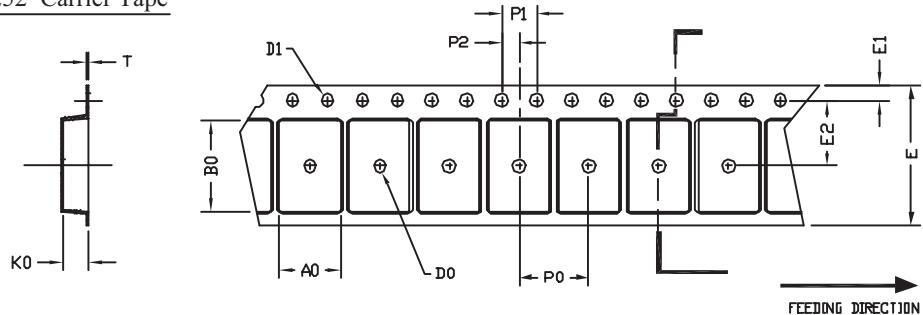
STU/D1855PL

TO251 Tube/TO-252 Tape and Reel Data

TO-251 Tube



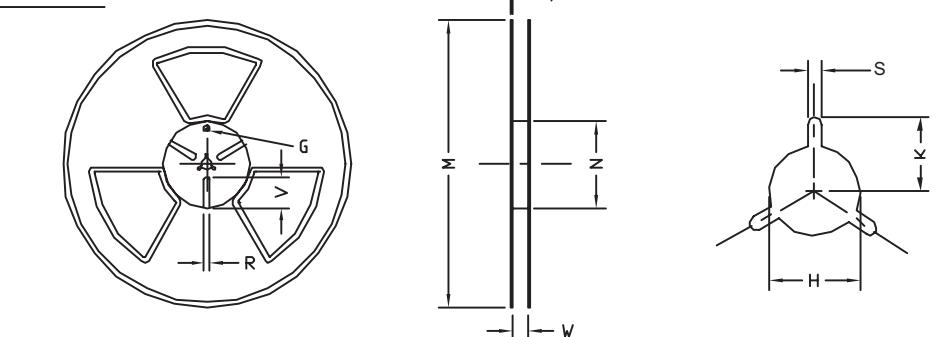
TO-252 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T	
TO-252 (16 mm)	6.80 ±0.1	10.3 ±0.1	2.50 ±0.1	ϕ 2	ϕ 1.5 + 0.1 - 0	16.0	0.3±	1.75	7.5 ±0.15	8.0 ±0.1	4.0 ±0.1	2.0 ±0.15	0.3 ±0.05

TO-252 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	T	H	K	S	G	R	V
16 mm	ϕ 330	ϕ 330 ± 0.5	ϕ 97 ± 1.0	17.0 + 1.5 - 0	2.2	ϕ 13.0 + 0.5 - 0.2	10.6	2.0 ± 0.5	---	---	---